| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|----------|------|---|---|---------------------|---------|------------------|
| S10 9 | 25 | (michael near2 tischler or thomas near2 kuech or robert near2 vaudo). in. and remov\$5 near10 substrate and (gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 19:51 |
| S10 8 | 35 | (michael near2 tischler or thomas near2 kuech or robert near2 vaudo). in. and remov\$5 near10 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR · | ON | 2005/06/23 19:51 |
| S11 1 | 3 | ("4622083" "4727047" "4931132"). PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/23 19:53 |
| S11 4 | 44 | lateral near10 (Gan or gallium near2 nitride) and @py<"2000" | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/23 19:54 |
| S11 3 | 2 | lateral near4 grow\$6 near10 (Gan or gallium near2 nitride) and @py<"2000" | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/23 19:54 |
| S11 2 | 393 | lateral near4 grow\$6 near10 (Gan or gallium near2 nitride) | US-PGPUB; USPAT; USOCR | OR. | ON | 2005/06/23 19:54 |
| S11 6 | 3074 | etch near2 stop near10 thick\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 19:57 |
| S11 5 | 4 | ("4931132" "4622083").pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 19:57 |
| S11 0 | 24 | (michael near2 tischler or thomas near2 kuech or robert near2 vaudo). in. and remov\$5 near10 substrate and (gan or gallium near2 nitride) near10 single near2 crystal\$7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 19:57 |
| S11 7 | 2 | etch near2 stop near10 thick\$5 near15 (Gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:06 |
| S11 8 | 54 | etch near2 stop near10 thick\$5 and (Gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:09 |

| S11 9 | 43 | etch near2 stop near10 (boron near2 nitride or bn) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:11 |
|----------|-----|---|---|------|----|------------------|
| S12 0 | 2 | etch near2 stop near10 (boron near2 nitride or bn) near15 thick\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:13 |
| S12 2 | 43 | etch near2 stop near10 (boron near2 nitride or bn) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:14 |
| S12 1 | 8 | stop near10 (boron near2 nitride or bn) near15 thick\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 20:14 |
| S12 3 | 8 | etch near2 stop near10 (boron near2 nitride or bn) and etch near2 stop near10 thick\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:35 |
| L3 | 422 | remov\$5 near5 (substrate or sapphire) and single near2 crystal\$6 near5 (gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:46 |
| L2 | 459 | remov\$5 near5 (substrate or sapphire) and single near2 crystal\$6 near10 (gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR . | ON | 2005/06/24 12:46 |
| L1 | 519 | remov\$5 near15 (substrate or sapphire) and single near2 crystal\$6 near10 (gan or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR . | ON | 2005/06/24 12:46 |
| L4 | 46 | remov\$5 near5 (substrate or sapphire) and single near2 crystal\$6 near5 (gan or gallium near2 nitride) and @py<"2000" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:49 |
| L5 | 3 | single near2 crystal\$6 near5 (gan or gallium near2 nitride) and @py<"2000" and 117/97.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:50 |

| L8 | 370 | (gan or gallium near2 nitride) and @py<"2000" and (substrate or wafer) near5 remov\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |
|-----|-----|--|---|----|----|------------------|
| L7 | 458 | (gan or gallium near2 nitride) and @py<"2000" and (substrate or wafer) near10 remov\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |
| L6 | 7 | (gan or gallium near2 nitride) and @py<"2000" and 117/97.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |
| L11 | 105 | (gan or gallium near2 nitride) near10 (crystal\$6 or crystallin\$5) and @py<"2000" and (substrate or wafer) near5 remov\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:52 |
| L12 | 6 | (gan or gallium near2 nitride) near10 (crystal\$6 or crystallin\$5) and @py<"2000" and (substrate or wafer) near5 sacrific\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:53 |